

# Citations for Ion : **B**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
<b>1952</b>	Lillie, A. B. 'The Disintegration of Oxygen and Nitrogen by 14.1 MeV Neutrons.' <i>Phys. Rev.</i> , 87, 716-22 (1952) <i>Comment</i> : R. 0.5-5 MeV 13C, 0.5-7 MeV 11B -> Air	1952-Lill
<b>1953</b>	Barkas, W. H. 'The Range Correction for Electron Pick-Up' <i>Phys. Rev.</i> , 89, 1019-22 (1953) <i>Comment</i> : R. 4-22 MeV 8Li, 8-16 MeV 8B -> Emulsion	1953-Bark
<b>1960</b>	Cao XuanChuan, C 'Relations Experimentales Parcours-Energie Pour Les Ions Legers De Faible Energie Dans Les Emulsions Nucleaires' <i>J. Phys. Radium</i> , 21, 757-59 (1960) <i>Comment</i> : R. 2.2-6.3 MeV 11B, 2.2-5.0 MeV 13C -> Emulsion	1960-Cao
<b>1960</b>	Northcliffe, L. C. 'Energy Loss and Effective Charge of Heavy Ions in Aluminum' <i>Phys. Rev.</i> , 120, 1744-57 (1960) <i>Comment</i> : S. 4-200 MeV He, B, C, N, O, F, Ne -> Al. Shows Stopping goes as (V/VoZ*2/3) but doesn't give Bohr (1941) credit.	1960-Nort
<b>1960</b>	Roll, P. G. Steigert, F. E. 'Energy Loss of Heavy Ions in Nickel, Oxygen and Nuclear Emulsion' <i>Nucl. Phys.</i> , 17, 54-66 (1960) <i>Comment</i> : S. He, B, C, N, O, F, Ne (2-10 MeV/amu) -> O, Ni, Emulsion	1960-Roll
<b>1960</b>	Roll, P. G. Steigert, F. E. 'Characteristics of Heavy Ion Tracks in Nuclear Emulsion' <i>Nucl. Phys.</i> , 16, 534-44 (1960) <i>Comment</i> : R. (2-200 MeV) He, B, C, N, O, F, Ne -> Emulsion	1960-Roll2
<b>1960</b>	Schambra, P. E. Rauth, A. M. Northcliffe, L. C. 'Energy Loss Measurements for Heavy Ions in Mylar and Polyethylene' <i>Phys. Rev.</i> , 120, 1758 (1960) <i>Comment</i> : S. He, B, Be, C, N, O, F, Ne (10 MeV/amu) -> Mylar, Polyethylene	1960-Scha2
<b>1962</b>	Teplova, Ya. A. Nikolaev, V. S. Dimitriev, I. S. Fateeva, L. N. 'Slowing Down of Multicharged Ions in Solids and Gases' <i>Zh. Eksp. Teor. Fiz.</i> , 42, 44-60 (1962)[ <i>Engl. Trans. Sov. Phys., JETP</i> 15, 31-41 (1962)] <i>Comment</i> : S, R.(75-1500 keV/amu) He, Li, Be, B, C, N, O, Ne, Na, Mg, Al, P, Cl, K, Br, Kr -> H2, He, CH4, Benzene, Air, Ar, S. Same -> Al, Ni, Ag, Au	1962-Tepl
<b>1963</b>	Ormrod, J. H. Duckworth, H. E. 'Stopping Cross Sections in Carbon for Low-Energy Atoms with Z < 12' <i>Can. J. Phys.</i> , 41, 1424-42 (1963) <i>Comment</i> : S. (10-130 keV) H, He, Li, Be, B, C, N, O, F, Ne, Na, Mg -> C	1963-Ormr

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<b>1965</b>	Bethge, K. Sandner, P. 'Zum Energieverlust Schwerer Ionen' <i>Phys. Letters, 19, 241-43 (1965)</i> <i>Comment : S. 5-20 MeV B, 7-28 MeV N -&gt; Ag, Ni, Au</i>	1965-Beth
<b>1965</b>	Ormrod, J. H. Macdonald, J. R. Duckworth, H. E. 'Some Low-Energy Atomic Stopping Cross Sections' <i>Can. J. Phys., 43, 275-84 (1965)</i> <i>Comment : S. (10-150 keV) H, D, He, Li, B, C, N, O, F, Ne, Na -&gt; Al; (20-130 keV) Si, P, S, Cl, Ar, K -&gt; C</i>	1965-Ormr
<b>1966</b>	Bethge, K. Sandner, P. Schmidt, H. 'Energieverluste und Ladungszustände Schwerer Ionen Beim Durchgang Durch Materie' <i>Z. Naturforschg. 21A, 1052-57 (1966)</i> <i>Comment : S. 5-20 MeV B, 5-30 MeV O, 7-28 MeV N, 5-30 MeV S -&gt; Ni, Ag, Au</i>	1966-Beth
<b>1966</b>	Macdonald, J. R. Ormrod, J. H. Duckworth, H. E. 'Stopping Cross Section in Boron of Low Atomic Number Atoms with Energies from 15 to 140 keV' <i>Z. Naturforschg. 21A, 130-34 (1966)</i> <i>Comment : S. (12-140 keV) H, D, He, Li, B, C, N, O, F, Ne, Na -&gt; B</i>	1966-Macd
<b>1967</b>	Large, L. N. Hill, H. Ball, M. P. 'Profiles of High Conductivity Shallow Layers in Silicon Produced by Boron Ion Implantations' <i>Int. J. Elec., 22, 153-64 (1967)</i> <i>Comment : R, dR. 25-125 keV B -&gt; Si</i>	1967-Larg
<b>1968</b>	Davies, D. E. 'Range and Distribution of Implanted Boron in Silicon' <i>Appl. Phys. Letters, 13, 243-45 (1968)</i> <i>Comment : R, dR. 200-400 keV B -&gt; Si</i>	1968-Davi
<b>1968</b>	Eisen, F. H. 'Channeling of Medium-Mass Ions through Silicon' <i>Can. J. Phys., 46, 561-72 (1968)</i> <i>Comment : S. 100-500 keV B, C, N, O, F, Ne, Na, Mg, Al, Si, P, Cl, Ar, K -&gt; Si (Cryst.)</i>	1968-Eise
<b>1968</b>	Hvelplund, P. 'Prisopgave' <i>Aarhus University P. 1-105 (In Danish) (1968)</i> <i>Comment : S, dS. Many Ions (H-Hg) at 50-500 keV -&gt; H, He, Ne, Ar, Kr, Xe, Air</i>	1968-Hvel
<b>1968</b>	Kleinfelder, W. J. Johnson, W. S. Gibbons, J. F. 'Impurity Distribution Profiles in Ion-Implanted Silicon' <i>Can. J. Phys., 46, 597-606 (1968)</i> <i>Comment : R, dR. 10-70 keV B, N, P, As -&gt; Si (Cryst.)</i>	1968-Klei

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1968	Ormrod, J. H. 'Low-Energy Electronic Stopping Cross Sections in Nitrogen and Argon' <i>Can. J. Phys.</i> , 46, 497-502 (1968) <i>Comment</i> : S. (5-200 keV) H, D, He, B, C, N, O, F, Ne -> N, Ar	1968-Ormr
1968	Roosild, S. Dolan, R. Buchanan, B. 'Semiconductor Doping by High Energy 1 - 2.5 MeV Ion Implantation.' <i>J. Electrochem. Soc.</i> , 115, 307-11 (1968) <i>Comment</i> : R, dR. 1-2.5 MeV B, 1-1.6 MeV N, 1 MeV P -> Si. Electrical Junction Measurements.	1968-Roos
1968	Volod'ko, V. G. Zorin, E. I. Pavlov, P. V. Tetel'Baum, D. I. 'Distribution and Range of Boron and Phosphorus Ions used in Bombardment of SiO <sub>2</sub> ' <i>Fiz. Tverd. Tela</i> , 10, 1048-52 (1968) [Engl. Trans. Sov. Phys. Solid State, 10, 828-31 (1968)] <i>Comment</i> : R, dR. 30-100 keV B, 50-150 keV P -> SiO <sub>2</sub>	1968-Volo
1968	Zorin, E. I. Pavlov, P. V. Tetelbaum, D. I. 'Investigation of Boron Atom Distribution in Silicon Doped by Ion Bombardment Method' <i>Fiz. Tverd. Tela</i> , 9, 3642-44 (1967). [Engl. Trans. Sov. Phys. Solid State, 9, 2874-76 (1968)]. <i>Comment</i> : R, dR. 20-60 keV B -> Si	1968-Zori
1969	Andreev, V. N. Nedopekin, V. G. Rogov, V. I. 'Long-Range Particles with Z > 2 in Ternary Fission of U235 by Thermal Neutrons' <i>Yaderna Fiz.</i> , 8, 38-49 (1969). [Eng. Trans. Sov. J. Nucl. Phys., 8, 22-28 (1969)] <i>Comment</i> : S. 0.06-3.0 MeV Li, B; 0.2-10 MeV Ne, 0.1-7 MeV N -> Ar	1969-Andr
1969	Davies, D. E. 'Range of Implanted Boron, Phosphorus, and Arsenic in Silicon' <i>Can. J. Phys.</i> , 47, 1750-53 (1969) <i>Comment</i> : R, dR. 0.15-1.8 MeV B, 1.0-1.7 MeV As, 0.5-1.7 MeV P -> Si	1969-Davi
1969	Fairfield, J. M. Crowder, B. L. 'Ion Implantation Doping of Silicon for Shallow Junctions' <i>Trans. Met. Soc. Aime</i> , 245, 469-473 (1969) <i>Comment</i> : R, dR. 70-280 keV B, P, 80-480 keV As -> Si	1969-Fair
1969	Macdonald, J. R. Sidenius, G. 'The Total Ionization in Methane of Ions with 1 <= Z1 <= 20 at Energies from 10 to 120 keV' <i>Phys. Letters A</i> , 28, 543-44 (1969) <i>Comment</i> : S. 10-120 keV H, He, Li, Be, B, C, N, O, F, Ne, Na, Mg, Al, Si, P, S, Cl, Ar, Ca, V, Sc, Ti -> CH <sub>4</sub>	1969-Macd

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1970	Bader, R. Kalbitzer, S. 'Low Energy Boron and Phosphorus Implants in Silicon. (B). Doping Profiles.' <i>Rad. Effects, 6, 211-16 (1970)</i> <i>Comment : R, dR. 6 keV B, 15 keV P -&gt; Si (Cryst.).</i>	1970-Bade
1970	Cairns, J. A. Holloway, D. F. Nelson, R. S. 'Measurement of Implanted Boron Concentration Profiles in Silicon by the Use of Heavy Ion X-Ray Excitation' <i>Proc. of the European Conference on Ion Implantation. Peter Peregrinus, Publisher, Stevenhage, England, P. 203-06 (1970)</i> <i>Comment : R, dR. 40, 100 keV B -&gt; Si</i>	1970-Cair
1970	Cairns, J. A. Nelson, R. S. Briggs, J. S. 'The Use of the Ion-Induced X-Rays to Investigate the Concentration Distribution and Atom Location of Boron-Implanted Silicon, in I' <i>Ruge and J. Graul (Ed.): Ion Implantation in Semiconductors. Springer, Berlin, P. 299-306 (1970)</i> <i>Comment : R. 100-300 keV B -&gt; Si</i>	1970-Cair2
1970	Davies, D. E. 'The Implanted Profiles of Boron, Phosphorus, and Arsenic in Silicon from Junction Depth Measurements' <i>Solid-State Elec., 13, 229-237 (1970)</i> <i>Comment : R. 0.1-2.0 MeV B, P, As -&gt; Si</i>	1970-Davi
1970	Lecrosnier, D. P. Pelous, G. P. 'High Energy Boron Implantation into Silicon' <i>Proc. of the European Conference on Ion Implantation. Peter Peregrinus, Publisher, Stevenhage, England, P. 106-06 (1970)</i> <i>Comment : R, dR. 1-2.5 MeV 11B -&gt; Si</i>	1970-Lecr
1970	Pistryak, V. M. Gnap, A. K. Kozlov, V. F. Garber, R. I. Fedorenko, A. I. 'Concentration Profile of Boron Ions Implanted into Silicon with Energies of 30 and 100 keV' <i>Fiz. Tverd. Tela, 12, 1281-82 (1970). [Engl. Trans. Sov. Phys. Solid State, 12, 1005-06 (1970).</i> <i>Comment : R, dR. 30, 100 keV B -&gt; Si (Cryst.)</i>	1970-Pist
1970	Stumpfi, W. Kalbitzer, S. 'Low Energy Boron and Phosphorus Implants in Silicon (a) Electrical Sheet Measurements' <i>Rad. Effects, 6, 205-210 (1970)</i> <i>Comment : R,dR. B, P (7 keV) -&gt; Si</i>	1970-Stum

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1971	Crowder, B. L. 'The Influence of the Amorphous Phase on Ion Distributions and Annealing Behavior of Group Iii and Group V Ions Implanted into Silicon' <i>J. Electrochem. Soc.</i> , 118, 943-52 (1971) <i>Comment</i> : R,dR. (50-300 keV) B, Al Ga, P, As, Sb, Bi -> Si	1971-Crow
1971	Gusev, V. M. Busharov, N. P. Demakov, K. D. Kozlow, Yu. G. 'Effects of Channeling on the Distribution of Electrically Active Boron and Phosphorus Atoms in Silicon Single Crystals' <i>Dokl. Akad. Nauk. Sssr</i> , 19, 319-22 (1971). [ <i>Engl. Trans. Sov. Phys. Doklady</i> , 19, 213-15 (1971)]. <i>Comment</i> : R, dR. 100 keV B, 150 keV P -> Si (Cryst. And Random)	1971-Guse
1971	Hogberg, G. 'Electronic and Nuclear Stopping Cross Sections in Carbon' <i>Phys. Stat. Sol. B</i> , 48, 829-41 (1971) <i>Comment</i> : S. (10-46 keV) Li, B, N, C, O, F, Ne, Na, P, Ar -> C	1971-Hogb
1971	Hvelplund, P. 'Energy Loss and Stragglng of 100-500 keV Atoms with 2 ó Z1 ó 12 in Various Gases' <i>Kgl. Danske Videnskab. Selskab Mat. Fys. Medd.</i> , 38, No. 4, P. 1-25 (1971) <i>Comment</i> : S,dS. (100-500 keV) He, Li, Be, B, C, N, O, F, Ne, Na, Mg -> Air, He, Ne, H2, O2	1971-Hvel
1971	Seidel, T. E. 'Distribution of Boron Implanted into Silicon' <i>In I. Ruge and J. Graul: Ion Implantation in Semiconductors. Springer, Berlin. p. 47-57 (1971)</i> <i>Comment</i> : R,dR. 30-300 keV 11B -> Si (Cryst. And Polycryst.)	1971-Seid
1971	Ziegler, J. F. Crowder, B. L. Kleinfelder, W. J. 'Experimental Evaluation of High Energy Ion Implantation Gradients for Possible Fabrication of a Transistor Pedastal Collector' <i>IBM J. Res. and Dev.</i> , 15, 452-456 (1971) <i>Comment</i> : R, dR. 2-4 MeV B, P -> Si	1971-Zieg
1972	Akasaka, Y. Horie, K. Kawazu, S. 'Lateral Spread of Boron Ions Implanted in Silicon' <i>Appl. Phys. Letters</i> , 21, 128-29 (1972) <i>Comment</i> : dR(Lateral). 75-250 keV B -> Si	1972-Akas
1972	Baccarani, G. Pickar, K. A. 'Range and Straggle of Boron in Photoresist' <i>Solid-State Elec.</i> , 15, 239-243 (1972) <i>Comment</i> : R, dR. 50-300 keV B -> Photoresist	1972-Bacc
1972	Davidson, S. M. 'Rapid Profile Measurements in Ion Implanted Silicon' <i>J. Phys. E</i> , 5, 23-26 (1972) <i>Comment</i> : R. 40 keV B -> Si (Anneal)	1972-Davi

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1972	Gittins, R. P. Morgan, D. V. Dearnaley, G. 'The Application of the Ion Microprobe Analyzer for the Measurements of the Distribution of Boron Ions Implanted into Silicon Crystals' <i>J. Phys. D: Appl. Phys.</i> , 5, 1654-63 (1972) <i>Comment</i> : R, dR. 200 keV Na, 110-400 keV B -> Si (Cryst. Chann. And Random)	1972-Gitt
1972	Hogberg, G. Skoog, R. 'Non-Evidence for Z1, Oscillations of the Nuclear Ion-Atom Interaction in an Amorphous Target' <i>Rad. Effects</i> , 13, 197-202 (1972) <i>Comment</i> : S. 50 keV Li, B, C, N, O, F, Ne, Na, Mg, P, Ar -> C	1972-Hogb
1972	Maul, J. Schulz, F. Wittmaack, K. 'Determination of Implantation Profiles in Solids by Secondary Ion Mass Spectrometry' <i>Phys. Letters A</i> , 41, 177-78 (1972) <i>Comment</i> : R. dR. 20-22 keV 11B -> Si (Amorphous)	1972-Maul
1972	Nishi, H. Sakurai, T. Furuya, T. 'Investigation of Boron Implanted Silicon by Backscattering Method. Defect and Impurity Distribution.' <i>Fujitsu Sci. and Tech. J.</i> , 8, 123-35 (1972) <i>Comment</i> : R, dR. 100 keV B -> Si	1972-Nish
1972	Pavlov, P. V. Zorin, E. I. Tetel'baum, D. I. Baranova, A. S. Vasil'Ev, V. K. 'On the Influence of Channeling and Anomalous Diffusion on the Profiles of Implanted Phosphorus and Boron Atoms Silicon' <i>Rad. Effects</i> , 13, 153-155 (1972) <i>Comment</i> : R. 40-100 keV P, B -> Si	1972-Pavl
1972	Sebilotte, P. Badanoin, M. Ndocko, V. B. Siffert, V. 'Low Energy Boron Implantation Profiles in Silicon from Junction Depth Measurements' <i>Rad. Effects</i> , 7, 7-15 (1972) <i>Comment</i> : R,dR. 15 keV B -> Si	1972-Sebi
1972	Wagner, S. 'Diffusion of Boron from Shallow Ion Implants in Silicon' <i>J. Electrochem. Soc.</i> , 119, 1570-1575 (1972) <i>Comment</i> : R, dR. 30 keV B -> Si [111]	1972-Wagn
1972	WestmorelandIii, J. E. 'Channeling Effect Analysis of Lattice Disorder in Boron Implanted Silicon' <i>Ph.D. Thesis, Cal. Inst. Tech., Unpublished</i> (1972) <i>Comment</i> : R, dR. 200, 300 keV B -> Si	1972-West

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1972	Ziegler, J. F. Crowder, B. L. Cole, G. W. Baglin, J. E. E. Masters, B. J. 'Boron Atom Distributions in Ion-Implanted Silicon by the (n,4He) Nuclear Reaction' <i>Appl. Phys. Letters, 21, 16-18 (1972)</i>	1972-Zieg
	<i>Comment : R,dR. 40-500 keV B -&gt; Si</i>	
1973	Akasaka, Y. Horie, K. 'Channeling Analysis and Electrical Behavior of Boron Implanted Silicon' <i>B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 145-57 (1973)</i>	1973-Akas
	<i>Comment : R,dR. 100 keV 11B -&gt; Si</i>	
1973	Akasaka, Y. Horie, K. Yoneda, K. Sakurai, T. Nishi, H. 'Depth Distribution of Defects and Impurities in 100-keV B+ Ion Implanted Silicon' <i>J. Appl. Phys., 44, 220-24 (1973)</i>	1973-Akas2
	<i>Comment : R, dR. 100 keV B -&gt; Si</i>	
1973	Bauer, L. -O. Macpherson, M. R. Robinson, A. T. Dill, H. G. 'Properties of Silicon Implanted with Boron Ions through Thermal Silicon Dioxide' <i>Solid-State Elec., 16, 289-300 (1973)</i>	1973-Baue
	<i>Comment : R, dR. B (40-100 keV) -&gt;Si Through SiO2</i>	
1973	Bulgakov, Yu. V. Nikolaev, V. S. Rogachev, Yu. V. 'Anomalous Energy Loss During Passage of Fast Boron Ions through Plane Channels in Single-Crystal Silicon' <i>Fiz. and Khim. Obrab. Mater. (Ussr), 5, 54-8 (1973)</i>	1973-Bulg
	<i>Comment : S. B (7.7 MeV) -&gt; Si (111) Channeled</i>	
1973	Combasson, J. L. Bernard, J. Guernet, G. 'Physical Profile Measurements in Insulating Layers using the Ion Analyzer' <i>B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 285-94 (1973)</i>	1973-Comb
	<i>Comment : R,dR. 60, 100 keV B -&gt; SiO2; 20, 40 keV B -&gt; Si3N4; 60 keV B -&gt; Si (Amorphous)</i>	
1973	Crowder, B. L. Ziegler, J. F. Cole, G. W. 'The Influence of the Amorphous Phase on Boron Atom Distributions in Ion Implanted Silicon' <i>B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 257-66 (1973)</i>	1973-Crow
	<i>Comment : R,dR. 50-150 keV 10B -&gt; Si. (Cryst. And Amorph.)</i>	
1973	Gibbons, J. F. 'Acceptor Profiles Obtained by Diffusive Redistribution of Implanted Impurities During Annealing' <i>Appl. Phys. Letters, 23, 49-51 (1973)</i>	1973-Gibb
	<i>Comment : R. 50 keV B -&gt; Si</i>	

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<b>1973</b>	Gibbons, J. F. Mylroie, S. 'Estimation of Impurity Profiles in Ion-Implanted Amorphous Targets using Joined Half-Gaussian Distributions' <i>Appl. Phys. Letters, 22, 568-569 (1973)</i> <i>Comment : R. 120 keV Sb, 60 keV B -&gt; Si</i>	1973-Gibb2
<b>1973</b>	Guerdtsiteli, I. G. Guldashvili, A. I. Disamidze, E. M. Zaslavsky, S. A. Kalinin, A. N. 'Implantation Angle Influence on Penetration of Boron Channeled Ions into Silicon' <i>Rad. Effects, 19, 171-74 (1973)</i> <i>Comment : R, dR. 30-200 keV B -&gt; Si (Cryst.)</i>	1973-Guer
<b>1973</b>	Guseva, M. T. Mansurova, A. N. 'Radiation-Enhanced Diffusion of Boron in Germanium During Ion Implantation' <i>Rad. Effects, 20, 207-10 (1973)</i> <i>Comment : R,dR. 30 keV B -&gt; Si</i>	1973-Guse
<b>1973</b>	Hofker, W. K. Werner, H. W. Oosthoek, D. P. DeGrefte, H. A. M. 'Influence of Annealing on the Concentration Profiles of Boron Implantations in Silicon' <i>Applied Phys., 2, 265-78 (1973)</i> <i>Comment : R, dR. 70 keV B -&gt; Si</i>	1973-Hofk
<b>1973</b>	Hofker, W. K. Werner, H. W. Oosthoek, D. P. DeGrefte, H. A. M. 'Profiles of Boron Implantation in Silicon Measured by Secondary Ion Mass Spectroscopy' <i>Rad. Effects, 17, 83-90 (1973)</i> <i>Comment : R. dR. 30-75 keV B -&gt; Si</i>	1973-Hofk2
<b>1973</b>	Hofker, W. K. Werner, H. W. Oosthoek, D. D. DeGrefte, H. A. M. 'Experimental Analysis of Concentration Profiles of Boron Implanted into Silicon' <i>B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 133-45 (1973)</i> <i>Comment : R,dR. 30-70 keV B -&gt; Si</i>	1973-Hofk3
<b>1973</b>	Kostka, A. Kalbitzer, S. 'Integrated dE-E Detector System made by Ion Implantation' <i>Appl. Phys. Letters, 23, 704-706 (1973)</i> <i>Comment : R. B (8 MeV), P (6 keV) -&gt; Si</i>	1973-Kost
<b>1973</b>	Kostka, A. Kalbitzer, S. 'Electrical Properties of Silicon Implanted with Boron Ions of MeV Energy' <i>Rad. Effects, 19, 77-82 (1973)</i> <i>Comment : R. B (3-8 MeV) -&gt; Si</i>	1973-Kost2



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1973	Mezey, G. Szokefalvi-Nagy, Z. Badinka, C. S. 'Measurement of the Boron Distribution in 10B-Implanted Silicon by the (n,alpha) Nuclear Reaction' <i>Thin Solid Films, 19, 173-175 (1973)</i> Comment : R, dR. 10-40 keV 10B -> Si	1973-Meze
1973	Okabayashi, H. Shinoda, D. 'Lateral Spread of 31P and 11B Ions Implanted in Silicon' <i>J. Appl. Phys., 44, 4220-21 (1973)</i> Comment : R, dR, dR(Lateral). 145, 260 keV 31P; 80, 150 keV 11B -> Si	1973-Okab
1973	Schulz, F. Wittmaack, K. Maul, J. 'Implications in the Use of Secondary Ion Mass Spectroscopy to Investigate Impurity Concentration Profiles in Solids' <i>Rad. Effects, 18, 211-15 (1973)</i> Comment : R, dR. 20 keV 11B -> Si	1973-Schu
1973	Schwartz, G. Trapp, M. Schimko, R. Butzke, G. Rogge, K. 'Concentration Profiles of Implanted Boron Ions in Silicon from Measurements with the Ion Microprobe' <i>Phys. Stat. Sol. A, 17, 653-58 (1973)</i> Comment : R, dR. 50-300 keV B -> Si	1973-Schw
1973	Wittmaack, K. Maul, J. Schulz, F. 'Energy Dependence and Annealing Behaviour of Boron Range Distributions in Silicon' <i>B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 119-31 (1973)</i> Comment : R,dR. 10-250 keV B -> Si	1973-Witt
1973	Wittmaack, K. Schulz, F. Maul, J. 'Nongaussian Range Profiles in Amorphous Solids' <i>Phys. Letters A, 43, 477-78 (1973)</i> Comment : R, dR. 100 keV 11B -> Si (Amorphous)	1973-Witt2
1973	Zohta, Y. 'Rapid Determination of Semiconductor Doping Profiles in Mos Structure' <i>Solid-State Elec., 16, 124-126 (1973)</i> Comment : R. 40 keV B -> SiO2, Si	1973-Zoht
1974	Bogancs, J. Deme, S. Gyulai, J. Nagy, A. Nazarov, V. M. 'A Method for the Determination of Boron Ranges in Ion Implanted Silicon by the 10B(n, Alpha) Nuclear Reaction' <i>Joint Institute for Nuclear Research. Dubna, Report No. P. 14-8295 (In Russian) (1974)</i> Comment : R. 20-80 keV B -> Si	1974-Boga

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1974	Darwish, M. Y. Luginbuhl, H. W. 'Carrier Mobility Profiles for Low-Dose Boron-Implanted Layers' <i>Appl. Phys. Letters, 25, 390-391 (1974)</i> <i>Comment : R. 150 keV B -&gt; SiO2</i>	1974-Darw
1974	Greene, J. E. Sequeda-Osorio, F. Streetman, B. G. Noonan, J. R. Kirpatrick, G. G. 'Measurement of Boron Impurity Profiles in Si using Glow Discharge Optical Spectroscopy' <i>Appl. Phys. Letters, 25, 435-38 (1974)</i> <i>Comment : R, dR. 120 keV B -&gt; Si</i>	1974-Gree
1974	Hildebrandt, D. Muller-Jahreis, U. 'Electronic Retarding Cross Sections of Light Ions in GaSb' <i>Int. J. Mass Spectrom. and Ion Phys. (Netherlands), 13, 177-9 (1974)</i> <i>Comment : S. 10-100 keV H, He, Li, B, C, N, O, F, Ne -&gt; GaSb</i>	1974-Hild
1974	Hofker, W. K. Werner, H. Oosthoek, D. P. Koeman, N. J. 'Boron Implantations in Silicon: A Comparison of Charge Carrier and Boron Concentration Profiles' <i>Appl. Phys., 4, 125-33 (1974)</i> <i>Comment : R, dR. 70 keV B -&gt; Si</i>	1974-Hofk
1974	Macdonald, P. J. Palmer, D. W. 'Differences in Defect Production and Annealing Processes in Boron- and Carbon-Irradiated Germanium' <i>Stuttgart, Et. Al., Lattice Defects in Semiconductors, Intl. Conf. on Semiconductors, 504-12 (1974)</i> <i>Comment : R, dR. 60 keV 11B, 12C -&gt; Ge</i>	1974-Macd
1974	Okabayashi, H. Daizaburo, S. 'Range and Standard Deviation of Ion-Implanted Phosphorus and Boron in Silicon' <i>NEC Res. and Dev., 35, 10-14 (1974)</i> <i>Comment : R, dR. 50-260 keV P, B -&gt; Si</i>	1974-Okab
1974	Pan, E. Fang, F. F. 'Lateral Spread of Ion Implanted Impurities in Silicon' <i>J. Appl. Phys., 45, 2801-2803 (1974)</i> <i>Comment : R. B, P (20-70 keV) -&gt; Si One of the earliest lateral-spread range measurements.</i>	1974-Pan
1974	Pistryak, V. M. Tetelbaum, D. I. Kozlov, V. F. Vasilev, V. K. Zorin, E. I. 'Influence of Amorphization on the Distribution of Boron Introduced into Silicon by Ion Bombardment' <i>Sov. Phys. Semicond., 7, 1325-1326 (1974)</i> <i>Comment : R. 100 keV B -&gt; Si</i>	1974-Pist

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1974	Prince, J. L. Schwetmann, F. N. 'Diffusion of Boron from Implanted Sources Under Oxidizing Conditions' <i>J. Electrochem. Soc.</i> , 121 705-710 (1974) <i>Comment</i> : R, dR. 80 keV B -> Si	1974-Prin
1974	Ryssel, H. Muller, H. Schmid, K. 'Damage Dependent Electrical Activation of Boron Implanted Silicon' <i>Applied Phys.</i> , 3, 321-24 (1974) <i>Comment</i> : R, dR. 34 keV B -> Si	1974-Ryss
1974	Sidenius, G. 'Systematic Stopping Cross Section Measurements with Low Energy Ions in Gases' <i>Kgl. Danske Videnskab. Selskab. Mat. Fys.Medd.</i> , 39, No. 4, 1-32 (1974) <i>Comment</i> : S. 0.6-70 keV H, He, 2-120 keV 6Li, 7Li, 3-120 keV Be, B, C, N, O, F, Ne -> CH4	1974-Side
1975	Biersack, J. Fink, D. 'Implantation of Boron and Lithium in Semiconductors Metals' <i>Ion Implantation in Semiconductors, Namba (ed.), Plenum, N. Y.</i> 211-18 (1975) <i>Comment</i> : R, dR. 50-150 keV 10B -> Si	1975-Bier
1975	Buhl, R. Huber, W. K. Lobach, E. 'Messung von Konzentrationsprofilen Dunner Schichten Mit der Sekundarionen-Massenspektrometrie (Sims)' <i>Vakuum-Technik</i> , 24, 189-94 (1975) <i>Comment</i> : R. 60, 100 keV B -> Si	1975-Buhl
1975	Dikii, N. P. Matyash, P. P. Skakun, N. A. 'Profiles of Radiation Damage and Implanted Boron in Silicon' <i>Sov. Phys. Semicond.</i> , 9, 395-96 (1975) <i>Comment</i> : R. 50 keV B -> Si	1975-Diki
1975	Gashtol'D, V. N. Gerasimenko, N. N. Dvurechenskii, A. V. Smirnov, L. S. 'Profiles of Defects Produced by the Implantation of Ions in Silicon' <i>Sov. Phys. Semicond.</i> , 9, 551-553 (1975) <i>Comment</i> : R. Profiles Of Defects (40-250 keV) Ar, B, P -> Si	1975-Gash
1975	Hendrickson, T. E. 'Ion Implanted Profiles from Two Point Spreading Resistance Measurements' <i>J. Electrochem. Soc.</i> , 122, 1539-1541 (1975) <i>Comment</i> : R. 150, 300 keV B -> Si ([100])	1975-Hend
1975	Hirao, T. Ohzone, T. Takayanagi, S. Horumi, H. 'Ion Implantation in Polycrystalline Silicon' <i>Ion Implantation in Semiconductors, Namba (ed.), Plenum, N. Y.</i> 599-604 (1975) <i>Comment</i> : R, dR. 50-150 keV B -> Si	1975-Hira

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1975	Hofker, W. K. 'Implantation of Boron in Silicon' <i>Philips Res. Repts. No. 8, P. 1-121 (1975)</i> <i>Comment : R,dR. 30-800 keV B -&gt; Si (Amorph., Polycryst.)</i>	1975-Hofk
1975	Hofker, W. K. Oosthoek, D. P. Koeman, N. J. DeGrefte, H. A. M. 'Concentration Profiles of Boron Implantations in Amorphous and Polycrystalline Silicon' <i>Rad. Effects, 24, 223-31 (1975)</i> <i>Comment : R,dR. 30-200 keV B -&gt; Si (Polycryst.), 70-800 keV B -&gt; Si (Amorph.)</i>	1975-Hofk2
1975	Oetzmann, H. Feuerstein, A. Grahmann, H. Kalbitzer, S. 'Range Parameters of Heavy Ions in Amorphous Targets at LSS-Energies of 0.0006 < Epsilon < 0.3.' <i>Phys. Letters, 55A, 170-172 (1975)</i> <i>Comment : R, dR. 1-60 keV As, Ge, Sb, Au, Bi -&gt; Si, Ge, Al</i>	1975-Oetz
1975	Ohmura, Y. Koike, K. Kobayashi, H. Murakami, K. 'Deviated Gaussian Profiles of Implanted Boron and Deep Levels in Silicon' <i>Ion Implantation in Semiconductors, Namba (ed.), Plenum, N. Y. 183-88 (1975)</i> <i>Comment : R, dR. 60-200 keV 10B, 11B -&gt; Si</i>	1975-Ohmu
1975	Ohmura, Y. Koike, K. 'Evidence for Electronic Stopping in Ion Implantation: Shallower Profile of Lighter Isotope 10B in Si' <i>Appl. Phys. Letters, 26, 221-22 (1975)</i> <i>Comment : R, dR. 50-200 keV 10B, 11B -&gt; Si</i>	1975-Ohmu2
1975	Schimko, R. Richter, C. E. Rogge, K. Schwartz, G. Trapp, M. 'Implanted Arsenic and Boron Concentration Profiles in SiO <sub>2</sub> Layers' <i>Phys. Stat. Sol. A, 28, 87-93 (1975)</i> <i>Comment : R,dR. 40-300 keV 11B, 40-150 keV 75As, -&gt; SiO<sub>2</sub></i>	1975-Schi
1975	Skakun, N. A. Dikii, N. P. Matyash, P. P. 'Some Characteristics of the Distribution of Radiation Defects Resulting from the Implantation of Boron Ions in Silicon' <i>Sov. Phys. Semicond., 8, 854-855 (1975)</i> <i>Comment : R. 50 keV B -&gt; Si</i>	1975-Skak
1975	Wittmaack, K. Schulz, F. Hietel, B. 'Range Distributions of Boron in Silicon Dioxide and the Underlying Substrate' <i>Ion Implantation in Semiconductors, Namba (ed.), Plenum, N. Y. 193-200 (1975)</i> <i>Comment : R, dR. 5-150 keV 11B -&gt; SiO<sub>2</sub></i>	1975-Witt
1975	Yudin, V. V. Kurinny, V. I. Akimov, Y. S. Karatsyuba, A. P. 'Spatial Distribution of Defects Produced by Boron Ion Implantation of Silicon' <i>Rad. Effects, 24, 59-61 (1975)</i> <i>Comment : R. 40 keV B -&gt; Si</i>	1975-Yudi

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1976	Anand, K. V. El-Dhaher, A. H. G. Sobhy, M. I. 'Distribution Profiles of Boron-Implanted Layers in Silicon using a High Resolution Anodic Oxidation Cell' <i>Int. J. Elec.</i> , 40, 617-623 (1976) Comment : R. 60-100 keV B -> Si	1976-Anan
1976	Blanchard, B. Combasson, J. L. Bourgoïn, J. C. 'Boron-Implanted Profiles in Diamond' <i>Appl. Phys. Letters</i> , 28, 7-8 (1976) Comment : R,dR. 40-250 keV B -> C (Diamond)	1976-Blan
1976	Grahmann, G. Kalbitzer, S. 'Nuclear and Electronic Stopping Powers of Low Energy Ions with $Z \leq 10$ in Silicon' <i>Nucl. Inst. Methods</i> , 132, 119-23 (1976) Comment : S. 2-60 keV H, He, B, C, N, Ne -> Si	1976-Grah
1976	Hoffman, I. Jager, E. Muller-Jahreis, U. 'Z1-Dependence of Electronic Energy Straggling of Light Ions' <i>Rad. Effects</i> , 31, 57 (1976) Comment : dS. 2 $\leq Z1 \leq 10$ (10-100 Kev) -> C, Si	1976-Hoff
1976	Kudoh, O. Uda, K. Ikushima, Y. Kamoshida, M. 'Impurity Profiles Within a Shallow P-N Junction by a New Differential Spreading Resistance Method' <i>J. Electrochem. Soc.</i> , 123, 1751-1754 (1976) Comment : R. 150 keV 11B -> Si P/N Junction	1976-Kudo
1976	Ligeon, E. Guivarc'H, A. 'Hydrogen Implantation in Silicon Between 1.5 - 60 keV.' <i>Rad. Effects</i> , 27, 129-37 (1976) Comment : S,R,dR. 1.5-60 keV H -> Si. S. 1.5-60 keV H, 2.0 MeV 11B -> Si	1976-Lige
1976	Marcyk, G. T. Streetman, B. G. 'Boron Impurity Profile Tailoring in Silicon by Ion Implantation Measurement by Glow Discharge Optical Spectroscopy' <i>J. Electrochem. Soc.</i> , 123, 1388-1391 (1976) Comment : R. 50-250 keV B -> Si	1976-Marc
1976	Ryssel, H. Kranz, H. Biersack, J. Muller, K. Henkelmann, R. A. 'Boron Profiles and Diffusion Behavior in SiO <sub>2</sub> -Si Structures' <i>Ion Implantation in Semiconductors</i> , Ed. by F. Chernow, J. A. Borders, D. K. Brice, 727-734 (1976) Comment : R. 30-150 keV B -> Si, SiO <sub>2</sub>	1976-Ryss
1977	Blamires, N. G. Smith, B. J. 'The Range of Doubly Charged Boron Ions' <i>J. Phys. D</i> , 10, 799-804 (1977) Comment : R. 80, 360 keV B -> Si, SiO <sub>2</sub>	1977-Blam

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1977	Datz, S. DelCampo, J. G. Dittner, P. F. Miller, P. D. Biggerstaff, J. A. 'Higher-Order Z1 Effects and Effects of Screening by Bound K-Electrons on the Electronic Stopping of Channeled Ions' <i>Phys. Rev. Letters</i> , 38, 1145-1148 (1977) <i>Comment</i> : S. 2 MeV/amu H, He, Li, Be, B, C, N, O, F, 3.5 MeV/amu H, He, Li, Be, B -> Au [111]	1977-Datz
1977	Datz, S. Gomez del Campo, J. Dittner, P. F. Miller, P. D. Biggerstaff, J. A. 'Higher Order Z1 Effects and Effects of Screening by Bound k-electrons on the Electronic Stopping of Channeled Ions' <i>Phys. Rev. Letters</i> , 38, 1145-1148 (1977) <i>Comment</i> : S. H, He, Li, Be, B (3.5 MeV/amu) -> Au Channeled stopping powers.	1977-Datz2
1977	Lecrosnier, D. Paugam, J. Gallou, J. 'Channeling of Boron Ions into Silicon' <i>Appl. Phys. Letters</i> , 30, 323-25, (1977) <i>Comment</i> : R, dR. 50 keV-1.8 MeV B -> Si	1977-Lecr
1977	Mertens, P. 'Energy Loss of Light 100 - 300 keV Ions in Thin Metal Foils' <i>Nucl. Inst. Methods</i> , 149, 149-153 (1978) <i>Comment</i> : S, dS.H, He, Li, Be, B, C, N, O, F, Ne (300 keV) -> C, Ni, Co, Nb. 300 keV He, Ne, F, O, N -> C, Al, Ti, Mn, Fe, Co, Ni, Cu, Nb, Ag, Au	1977-Mert
1977	Ricco, R. P. Goldstein, J. I. McCallum, J. G. 'The Diffusion of Implanted Boron in Silicon' <i>J. Electrochem. Soc.</i> , 124, 276-279 (1977) <i>Comment</i> : R. 300 keV B -> Si (Diffusion At 1000 Deg C)	1977-Ricc
1977	Ryssel, H. Kranz, H. Muller, K. Henkelmann, R. A. Biersack, J. 'Comparison of Range and Range Stragglings of Implanted 10B and 11B in Silicon' <i>Appl. Phys. Letters</i> , 30, 399-401, (1977) <i>Comment</i> : R, dR. 20-200 keV 10B, 11B -> Si	1977-Ryss
1977	Shimizu, R. Kang, S. T. Koshikawa, T. Ogata, H. Kanayama, K. 'Monte Carlo Simulation of Depth and Lateral Profiles of Boron Atoms Implanted in Polycrystalline Silicon' <i>J. Appl. Phys.</i> , 48, 1745-47 (1977) <i>Comment</i> : R, dR. 150 keV B -> Si.	1977-Shim
1977	Thompson, D. A. Robinson, J. E. Walker, R. S. 'Inelastic Stopping of Medium Energy Light Ions in Silicon' <i>Rad. Effects</i> , 32, 169-175 (1977) <i>Comment</i> : dS,R,dR. 10-80 keV H, He, Li, B, C, N, O, Ne -> Si	1977-Thom
1978	Furuya, T. Nishi, H. Inada, T. Sakurai, T. 'Channeled-Ion Implantation of Group-III and Group-V Ions into Silicon' <i>J. Appl. Phys.</i> , 49, 3918-3921 (1978). <i>Comment</i> : R, dR. 100-300 keV B, P, As, Al, Ga -> Si [111], [110], Random	1978-Furu

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1978	Marcovich, A. Bahir, G. Bernstein, T. Kalish, R. 'A Method for Measuring Stopping Powers of Channeled Ions: Boron in Si' <i>Rad. Effects, 39, 65-70 (1978)</i> <i>Comment : S, dS. 350-400 keV B -&gt; Si</i>	1978-Marc
1978	North, J. C. Adams, A. C. Richards, G. F. 'Ion Implantation Doping of Polycrystalline Silicon' <i>Extend. Abs. Electrochem., 78, 540 (1978)</i> <i>Comment : R. 150 keV B, As; 300 keV P -&gt; Si</i>	1978-Nort
1978	Onheiser, P. Zaruba, I. Cervena, J. Hnatowicz, V. Kosina, Z. 'A Study of Boron Ion Implanted Profiles in Silicon from 10B(n,alpha)7Li Reaction Product Spectra' <i>Intl. Conf. Ion Beam Modification of Materials, Budapest -b (1978)</i> <i>Comment : R, dR. 50-400 keV B -&gt; Si</i>	1978-Onhe
1978	Rao, E. V. K. Duhamel, N. Favennec, P. N. L'Haridon, H. 'Investigation of Compensation in Implanted N-GaAs' <i>J. Appl. Phys., 49, 3898-3905 (1978)</i> <i>Comment : R, dR. 200 keV-1 MeV H, B, As -&gt; GaAs</i>	1978-Rao
1978	Tsai, M. Y. Streetman, B. G. Williams, P. Evans, C. A. 'Anomalous Migration of Fluorine and Electrical Activation of Boron in BF <sub>2</sub> -Implanted Silicon' <i>Appl. Phys. Letters, 32, 144-147 (1978)</i> <i>Comment : R. 150 keV BF<sub>2</sub>+ -&gt; Si</i>	1978-Tsai
1978	Ullrich, B. M. Mayer, J. W. 'Straggling of MeV Ions in Osmium' <i>Boehm. Phys. Gess. J., 1, 478-489 (1978)</i> <i>Comment : S, dS. 2-50 MeV H, He, Li, Be, B, C, N, O -&gt; Os</i>	1978-Ullr
1978	White, C. W. Christie, W. H. Appleton, B. R. Wilson, S. R. Pronko, P. P. 'Redistribution of Dopants in Ion-Implanted Silicon by Pulsed-Laser Annealing' <i>Appl. Phys. Letters, 33, 662-664 (1978)</i> <i>Comment : R, dR. 35 keV 11B, 80 keV 31P, 100 keV 75As -&gt; Si</i>	1978-Whit
1978	Wilson, R. G. Dunlap, H. L. Jamba, D. M. 'Angular Sensitivity of Controlled Implanted Doping Profiles' <i>NBS Special Publication 400-49 (1978).</i> <i>Comment : R, dR. 20 - 150 keV B -&gt; Si</i>	1978-Wils2
1978	Young, R. T. White, C. W. Clark, G. J. Narayan, J. Christie, W. H. 'Laser Annealing of Boron-Implanted Silicon' <i>Appl. Phys. Letters, 32, 139-141 (1978)</i> <i>Comment : R. 35 keV B -&gt; Si (Compares Laser And Conventional Annealing)</i>	1978-Youn

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1979	Comas, J. Wilson, R. G. 'Channeling and Random Equivalent Depth Distributions of 150 keV Li, Be, and B Implanted in Si' <i>Preprint (1979) 2</i> <i>Comment : S, R, dR. 150 keV Li, Be, B -&gt; Si</i>	1979-Coma
1979	Hirao, T. Inoue, K. Takayanagi, S. Yaegashi, Y. 'The Concentration Profiles of Projectiles and Recoiled Nitrogen in Si after Ion Implantation through Si <sub>3</sub> N <sub>4</sub> Films' <i>J. Appl. Phys., 50, 193-201 (1979)</i> <i>Comment : R, dR. 160 keV P -&gt; Si, 355 keV As -&gt; Si, 50 keV B -&gt; Si, 200 keV Ar -&gt; Si</i>	1979-Hira2
1979	Pham, M. T. 'A Very Simple Method for Profiling the Ion-Implanted Si-Surface' <i>Phys. Stat. Sol. A, 49, 261-265 (1979)</i> <i>Comment : R. 30 keV Si, P, B, Ar, As; 12.2 keV In -&gt; Si</i>	1979-Pham
1979	Tsai, M. Y. Day, D. S. Streetman, B. G. Williams, P. Evans, Jr. C. A. 'Recrystallization of Implanted Amorphous Silicon Layers. II. Migration of Fluorine in BF <sub>2</sub> -Implanted Silicon.' <i>J. Appl. Phys., 50, 188-192 (1979)</i> <i>Comment : R, dR. 50-200 keV 28Si, 25-85 keV 11B, 150 keV BF<sub>2</sub> -&gt; Si</i>	1979-Tsai
1979	Wada, Y. Hashimoto, N. 'Anomalous Carrier Tail Generation Mechanism in BF <sub>2</sub> Ion-Implanted Layers of Silicon' <i>J. Appl. Phys., 50, 6257-6261 (1979)</i> <i>Comment : R, dR. 178 keV BF<sub>2</sub> Implanted Into Si (Carrier Profiles).</i>	1979-Wada
1979	Wada, Y. Hashimoto, N. 'Anomalous Carrier Profiles in BF <sub>2</sub> Ion-Implanted Silicon' <i>J. Appl. Phys., 50, 5720-25 (1979)</i> <i>Comment : R, dR. 40 keV B-&gt;Si.</i>	1979-Wada2
1979	White, C. W. Christie, W. H. Pronko, P. P. Appleton, B. R. Wilson, S. R. 'Dopant Profile Changes Induced by Pulsed Laser Annealing' <i>Rad. Effects, 47, 37-40 (1979)</i> <i>Comment : R, dR. 35-150 keV B, P, As, Sb, Cu, Fe -&gt; Si</i>	1979-Whit
1979	Williamson, K. R. Theis, W. M. Yun, S. S. Park, Y. S. Ehret, J. E. 'Glow-Discharge Optical Spectroscopy Measurement of B-, Ge-, and Mg- Implanted GaAs' <i>J. Appl. Phys., 50, 8019-8024 (1979)</i> <i>Comment : R, dR. 60-120 keV B, Ge, Mg -&gt; GaAs</i>	1979-Will
1980	Gat, A. Gerzberg, L. Gibbons, J. F. Lietoila, A. Johnson, N. M. 'Annealing of Ion-Implanted Si using a Scanned CW Laser System' <i>Rad. Effects, 48, 195-202 (1980)</i> <i>Comment : R, dR. 35 keV B -&gt; Si</i>	1980-Gat



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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1980	Josquin, W. J. M. J. 'The Oxidation Characteristics of Nitrogen-Implanted Silicon' <i>Rad. Effects, 47, 221-224, (1980)</i> <i>Comment : R, dR. 250-800 keV H, H2, He, B, P -&gt; Si</i>	1980-Josq
1980	Komarov, F. F. Kuryazov, V. D. Solovev, V. S. Shiryayev, S. Yu. 'Formation of Structure Defects and Behavior of Ion-Implanted Boron in Silicon Under Annealing in Various Ambients' <i>Phys. Stat. Sol. A, 58, 99-105 (1980)</i> <i>Comment : R, dR. 100 keV B -&gt; Si</i>	1980-Koma
1980	Muller, K. Henkelmann, R. Jahnel, F. Ryssel, H. Habberger, K. 'The Application of the (n, $\alpha$ )-Method of Boron Depth Profiling and Channeling - Blocking Measurement in Semiconductor Materials' <i>Preprint (1980) 6</i> <i>Comment : R, dR. 60-210 keV B -&gt; Si, SiO2</i>	1980-Mull
1980	Myers, D. R. Wilson, R. G. 'Alignment Effects on Implantation Profiles in Silicon' <i>Rad. Effects, 47, 91-94 (1980)</i> <i>Comment : R, dR. 300 keV B -&gt; Si</i>	1980-Myer
1980	Ryssel, H. Hoffman, K. Habberger, K. Prinke, G. Muller, K. 'High Concentration Effects of Ion Implanted Boron in Silicon' <i>IEEE Trans. Nucl. Sci., NS-26, 378-379 (1980)</i> <i>Comment : R, dR. 120 keV B -&gt; Si</i>	1980-Ryss
1980	Ryssel, H. Muller, K. Biersack, J. Kruger, W. Lang, G. 'Range and Range Straggling of Ion-Implanted Boron in Cd0.2-Hg0.8-Te' <i>Phys. Stat. Sol. A, 57, 619-624 (1980)</i> <i>Comment : R, dR. 60-400 keV B -&gt; Cd</i>	1980-Ryss2
1980	Sofield, C. J. Cowern, N. E. B. Freeman, J. M. 'Charge-Exchange Effects in Energy-Loss Straggling' <i>Nucl. Inst. Methods, 170, 221-225 (1980)</i> <i>Comment : R, dR. 0-50 MeV Atomic Numbers 1-16 -&gt; Al</i>	1980-Sofi
1982	Fahrner, W. R. Heidemann, K. Schottle, P. 'Results of Ion Implantation into Silicon in the 100 MeV Range' <i>Phys. Stat. Sol. A, 70, 463-472 (1982)</i> <i>Comment : R, dR. O, B (56-65 MeV) -&gt; Si</i>	1982-Fahr
1982	Mertens, P. Krist, Th. 'Stopping Ratios for 30 - 300 keV Ions with $1 \leq Z \leq 5$ ' <i>J. Appl. Phys., 53 (11), 7343 - 7349 (1982)</i> <i>Comment : S, H, He, Li, Be, B (30-330 keV) -&gt; C, V, Cr, Fe, Ni, Zn</i>	1982-Mert3

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
<b>1983</b>	Fink, D. Biersack, J. P. Stadele, M. Tjan, K. Cheng, V. K. 'Z2 Stopping Power Oscillations as Derived from Range Measurements' <i>Nucl. Inst. Methods, 218, 817-820 (1983)</i> <i>Comment : S, R, He, Li, B, N (50-1500 keV) -&gt; Various Metals (V to Bi)</i>	1983-Fink
<b>1983</b>	Wach, W. Wittmaack, K. 'Ranges of Low Energy Light Ions in Amorphous Silicon' <i>Phys. Rev. B, 27 (6), 3528-3537 (1983)</i> <i>Comment : R, dR, Li, B, N, O, F, Na, Mg, Al ((1-20 keV) -&gt; Si</i>	1983-Wach
<b>1984</b>	Adesida, I. Karapiperis, L. 'The Range of Light Ions in Polymeric Resists' <i>J. Appl. Phys., 56 (6), 1801-1807 (1984)</i> <i>Comment : R, dR, H, He, Li, Be, B, C (5-300 keV) -&gt; PMMA photoresist</i>	1984-Ades
<b>1984</b>	Byrne, P. F. Cheung, N. M. Tam, S. Hu, C. Shih, Y. C. 'Megavolt Boron and Arsenic Implantation into Silicon' <i>Mat. Res. Soc. Sym., 27,253-258 (1984)</i> <i>Comment : R, dR, B, As (4-11 MeV) -&gt; Si</i>	1984-Byrn
<b>1984</b>	Krist, Th. Mertens, P. 'Application of Brandt's Effective Charge Theory to Measurements for 50-350 keV Ions with $1 \leq Z_1 \leq 5$ ' <i>Nucl. Inst. Methods, B2, 119-122 (1984)</i> <i>Comment : S, H, He, Li, Be, B (50-350 keV) -&gt; C, Al, V, Cr, Fe, Ni, Cu, Zn, Ag, Pt, Au, Bi</i>	1984-Kris
<b>1984</b>	Rybka, V. Hnatowicz, V. Kvitek, J. Vacik, J. Schmidt, B. 'Determination of the Range Profiles of Boron Implanted into Si and SiO <sub>2</sub> ' <i>Phys. Stat. Sol. A, 83, 165-171 (1984)</i> <i>Comment : R, dR, B (30-200 keV) -&gt; Si, SiO<sub>2</sub></i>	1984-Rybk
<b>1985</b>	Fink, D. Biersack, J. P. Chen, J. T. Stadele, M. Tjan, K. 'Distributions of Light Ions and Foil Destruction after Irradiation of Organic Polymers' <i>J. Appl. Phys., 58, 668-676 (1985)</i> <i>Comment : R, H, He, Li, B, C, N, Bi (50-300 keV) -&gt; AZ111, PMMA, Epoxy, C, Li, PMCN</i>	1985-Fink
<b>1985</b>	Ingrahm, D. C. Baker, J. A. Walsh, D. A. 'Range Distributions of MeV Implants in Silicon' <i>Nucl. Inst. Methods, B7/8, 361-365 (1985)</i> <i>Comment : R, dR, B, P, Sb (0.4-6 MeV) -&gt; Si</i>	1985-Ingr
<b>1987</b>	Ingram, D. C. Baker, J. A. Walsh, D. A. Strathman, E. 'Range Distributions of MeV Implants in Silicon - 2' <i>Nucl. Inst. Methods, B21, 460-465 (1987)</i> <i>Comment : R, dR, B, P, Ga (0.4-6.0 MeV) -&gt; Si</i>	1987-Ingr

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
<b>1988</b>	Behar, M. Weiser, M. Kalbitzer, S. Fink, D. Grande, F. L. 'Implanted Boron Profiles in Silicon' <i>Nucl. Inst. Methods, B34, 316-320 (1988)</i> <i>Comment : R, dR. B (10-1000 keV) -&gt; Si</i>	1988-Beha
<b>1988</b>	Delfino, M. Morga, A. E. Maillot, P. Broadbent, E. K. 'Range Distributions of B in Co, CoSi <sub>2</sub> , Ti and TiSi <sub>2</sub> ' <i>J. Appl. Phys., 64 (2), 607-609 (1988)</i> <i>Comment : R, dR. B (10-120 keV) -&gt; Co, Ti, CoSi<sub>2</sub>, TiSi<sub>2</sub></i>	1988-Delf
<b>1988</b>	Kuronen, A. Raisanen, J. Keinonen, J. Tikkanen, P. Rauhala, E. 'Electronic Stopping Power for Li, B, C, N, O at Energies 0.4-2.1 MeV/amu in Ta and Au, and for C at energies 0.4-1.4 MeV/amu in 18 elemental solids' <i>Nucl. Inst. Methods, B35, 1-6 (1988)</i> <i>Comment : S. Li, B, C, N, O (0.4-2.1 MeV/amu) -&gt; Ta, Au</i>	1988-Kuro
<b>1988</b>	Wilson, R. G. '(111) Random and (110) Channeling Implantation Profiles and Range Parameters in HgCdTe' <i>J. Appl. Phys., 63, 5302-5311 (1988)</i> <i>Comment : R, dR. 45 Ions (H to Ta) at 100-700 keV -&gt; HgCdTe</i>	1988-Wils
<b>1988</b>	Wilson, R. G. 'Ion Implantation and SIMS Profiling of Impurities in II-VI Materials HgCdTe and CdTe' <i>J. Crystal Growth, 86, 735-743 (1988)</i> <i>Comment : R, dR. 52 Ions (H-Hg) at 100-700 keV -&gt; CdTe, HgCdTe</i>	1988-Wils2
<b>1989</b>	LaFerla, A. DiFranco, A. Rimini, E. 'Implants of 15-50 MeV Boron Ions into Silicon' <i>Matl. Sci. Eng., B2, 69-73 (1989)</i> <i>Comment : R, dR. B (15-50 MeV) -&gt; Si</i>	1989-LaFe
<b>1990</b>	Raisanen, J. Rauhala, E. 'Stopping Powers and Energy Loss of Mylar, Kapton, Havar and Ni for 10 Ions (Z= 3-17) in the Energy Range 0.2-2.1 MeV/amu' <i>Phys. Rev. B, 41, 3951-3958 (1990)</i> <i>Comment : S. B, C, N, O, Al, Si, P, Cl (0.2-2.1 MeV/amu) -&gt; Mylar, Kapton, Havar, Ni</i>	1990-Rais
<b>1990</b>	Rauhala, E. Raisanen, J. 'Stopping Powers of Li, B, C, O Ions in C <sub>16</sub> H <sub>14</sub> O <sub>3</sub> Polycarbonate' <i>Phys. Rev. B, 42, 3877-3880 (1990)</i> <i>Comment : S. Li, B, C, N, O (0.5-2.1 MeV/amu) -&gt; Polycarbonate</i>	1990-Rauh
<b>1991</b>	Kuronen, A. 'A Study of Stopping Power using Nuclear Methods' <i>Comm. Physico-Math. (Finland), 122, 1-36 (1991)</i> <i>Comment : S. Ion [Z=3-22] at (0-0.4 Vo) -&gt; Solids (Z=14-82)</i>	1991-Kuro

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1991	Raisanen, J. Rauhala, E. Bjornberg, M. Kiss, A. Z. Dominguez, J. 'Stopping Powers of Al and Sn for He, Li, B, C, N and O Ions in the Energy Range 0.5-2.6 MeV/amu' <i>Rad. Effects, 118 (2), 97-103 (1991)</i> <i>Comment : S. He, Li, B, C, N, O (0.5-2.6 MeV/amu) -&gt; Al, Sn</i>	1991-Rais
1992	Rauhala, E. Raisanen, J. Fulop, Zs. Kiss, A. Z. Hunyadi, I. 'Slowing Down of Light Ions in LR-115 Nuclear Track Material' <i>Nucl. Tracks Rad. Meas. (UK), 20, 611-614 (1992)</i> <i>Comment : S. H, He, Li, B, C, N, O (0.3-4.3 MeV/amu) -&gt; LR-115 (nuclear track material)</i>	1992-Rauh
1993	Goppelt, P. Biersack, J. P. Gebauer, B. Fink, D. Bohne, W. 'Range Measurements of Boron Isotopes in Silicon from 600 keV to 2 MeV' <i>Nucl. Inst. Methods, B80/81, 62-64 (1993)</i> <i>Comment : R. B (0.6-2.0 MeV) -&gt; Si</i>	1993-Gopp
1993	Jin, C. Lu, X. Huang, X. Ye, Y. Jiang, D. 'Stopping Powers of Heavy Ions in Silver' <i>Nucl. Sci Tech (China), 4, 241-244 (1993)</i> <i>Comment : S. B, C, F (0.11-0.53 MeV/amu) -&gt; Ag</i>	1993-Jin
1993	Jin, C. Lu, X. Huang, X. Ye, Y. Xia, Z. 'Stopping Power of Mylar for Low Velocity B-11, C-12 and O-16 Ions' <i>Phys. Rev. B, 48, 6858-5861 (1993)</i> <i>Comment : S. B, C, O (1.0-6.0 MeV) -&gt; Mylar</i>	1993-Jin 2
1994	Raisanen, J. Rauhala, E. Fulop, Z. Kiss, A. Z. Somorjai, E. 'Stopping Powers of CR-39 Nuclear Track Material for Z=1-14 Ions with 0.25-2.8 MeV/amu' <i>Rad. Meas. (UK), 23, 749-752 (1994)</i> <i>Comment : S. Z=1-14 (0.25-2.8 MeV/amu) -&gt; CR-39</i>	1994-Rais2
1994	Rauhala, E. Raisanen, J. 'Stopping Powers of Solid Hydrogen, Carbon and Oxygen for 0.5-2.1 MeV/amu Li-7, B-11, C-12, N-14 and O-16' <i>Nucl. Inst. Methods, B93, 399-403 (1994)</i> <i>Comment : S. Li, B, C, N, O (0.5-2.1 MeV/amu) -&gt; Solid H, C, O</i>	1994-Rauh
1995	Zhu, J. L. Chadderton, L. T. Fink, D. Cruz, S. A. Ghosh, S. 'Electronic Stopping and Etched Particle Tracks in Polymers: Boron and Lithium Tracks' <i>Nucl. Inst. Methods, B105, 208-211 (1995)</i> <i>Comment : S,R. B, Li (1.1-2.1 MeV) -&gt; CR-39</i>	1995-Zhu
1996	Gelfort, S. Kerkow, H. Stolle, R. Petukhov, V. P. Romanowski, E. A. 'Angular Dependence of the Electronic Energy Loss for Low Energy Heavy Ions under Channeling Conditions' <i>Nucl. Inst. Methods, B115, 315-318 (1996)</i> <i>Comment : S. Channeling of ions He to Kr in Si &lt;110&gt;</i>	1996-Gelf

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1996	Misdaq, M. A. Ellassali, R. 'Average Stopping Powers for Channeled Ions using Calculational and Experimental Methods' <i>Nucl. Inst. Methods, 119, 325-330 (1996)</i> Comment : S. Light ions -> Si, GaAs (channeled)	1996-Misd
1997	Dos Santos, J. H. R. Behar, M. Grande, P. L. Boudinov, H. Kalbitzer, S. 'Electronic Stopping Power of B in Si in Random and <100> Channeling Directions' <i>Phys. Rev., B55, 13651-13657 (1997)</i> Comment : S. B (500 - 9000 keV) -> Si Random and Channeled	1997-DosS
1998	Zhang, T. Lu, X. Xia, Z. Shen, D. 'Measured Stopping Power for B-11 Ions in Z = 6-47 Targets' <i>Phys. Rev. B, B57, 10213-10216 (1998)</i> Comment : S. B (0.5-5.2 MeV) -> C, Al, Ti, Cu, Nb, Ag,	1998-Zhan
1999	Angulo, C. Delbar, T. Graulich, J. S. Leleus, P. 'Stopping Power Measurements: Implications in Nuclear Astrophysics' <i>AIP Conf. Proc., 495, 381-384 (1999)</i> Comment : S. Be, B, C, N, O, F, Ne (1 MeV/u) -> C, Al, Ni, Ch2, PVC	1999-Angu
1999	Jiang, W. Grotzschel, W. Pilz, W. Schmidt, B Moller, W. 'Random and Channeling Stopping Powers and Charge State Distribtuions in Silicon for 0.2 - 1.2 MeV/u Positive Heavy Ions' <i>Phys. Rev. B, 59, 226-234 (1999)</i> Comment : S. Li, B, C, N, O, P, Cl (0.2 - 1.2 MeV/u) -> Si	1999-Jian
2000	Angulo, C. Delbar, Th. Graulich, J. -S. Leleux, P. 'Stopping Powers of Ions at 1 MeV per Nucleon' <i>Nucl. Instl. Methods, V170, 21-27 (2000)</i> Comment : S. Be, B, C, N, O, F, Ne (1 MeV/u) -> C, Al, Ni, CH2, PVC	2000-Angu
2000	Hu, B. Wu, Y. Zhang, X. Cheng, X. Liu, Z. 'The Energy Loss of C-12 and B-11 Ions in Seven Elements' <i>Nucl. Inst. Methods, B160, 195-202 (2000)</i> Comment : S. C, B (1 - 5 MeV) -> Co, Ni, In, Pd, Cd, Lu and Ta	2000-Hu
2001	Diwan, P. K. Sharma, A. Kumar, S. 'Stopping Power for Heavy Ions (2<Z1<36) in Solids at Energies about 0.5-2.5 MeV/u' <i>Nucl. Inst. Methods, B174, 267-273 (2001)</i> Comment : S. Li, B, N, F, Na, Mg (0.5 - 2.5 MeV/u) -> Pd, Gd, Lu, Ta, Au, Ni, Cr39, CR-39, Mylar, Kapton, LR-115, Havar, Polycarbonate	2001-Diwa
2001	Zhang, Y. Possnert, G. Whitlow, H. J. 'Measurements of the Mean Energy-Loss of Swift Heavy Ions in Carbon with High Precision' <i>Nucl. Inst. Methods, B183, 34-37 (2001)</i> Comment : S. Li, Be, B, C, N, O, F, Na, Mg, Al, Si, Cr, Mn, Fe (100 - 800 keV/u) -> C	2001-Zhan

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
<b>2002</b>	Whitlow, H. J. Timmers, H. Elliman, R. G. Weijers, T. D. Zhang, Y. 'Measurement and Uncertainties of Energy Loss in Silicon over a Wide Z1 Range using Time-of-Flight Detector Telescopes' <i>Nucl. Inst. Methods, B195, 133-146 (2002)</i> <i>Comment : S. Li, Be, B, C, N, O, F, Na, Mg, Al, Si, P, Mn, Fe -&gt; Si</i>	2002-Whit2
<b>2002</b>	Zhang, Y. 'High-Precision Measurement of Electronic Stopping Powers for Heavy Ions using High-Resolution Time-of-Flight Spectrometry' <i>Nucl. Inst. Methods, B196, 1-15 (2002)</i> <i>Comment : S. Stopping of 18 Heavy Ions into C, Al and Au Targets</i>	2002-Zhan
<b>2003</b>	Zhang, Yanwen Weber, W. J. 'Electronic stopping of He, B, N, and Al in SiC' <i>Appl. Phys. Lett. 83, 1665 (2003)</i> <i>Comment : S. He, B, N, Al (0.5 -0.6 MeV/n) -&gt; SiC</i>	2003-Zha2
<b>2004</b>	Hsu, J. Y. Yu, Y. C. Liang, J. H. Chen, K. M. Niu, H. 'Energy Loss of He, Li and B Isotopes with MeV Energies in Au' <i>Nucl. Inst. Methods, B219-220, 251-255 (2004)</i> <i>Comment : S. He, Li B -&gt; Au</i>	2004-Hsu
<b>2004</b>	Li, M. M. O'Connor, D. J. Timmers, H. 'A Study of the Charge State Approach to the Stopping Power of MeV B, N and O Ions in Carbon' <i>Nucl. Inst. Methods, B222, 11-18 (2004)</i> <i>Comment : S. B, N, O -&gt; C</i>	2004-Li
<b>2004</b>	Zhang, Y. Weber, W. Whitlow, H. J. 'Electronic Stopping Powers for Heavy Ions in Silicon' <i>Nucl. Inst. Methods, B215, 48-56 (2004)</i> <i>Comment : S. 14 light ions (Be-Cu) -&gt; Si</i>	2004-Zha3
<b>2005</b>	Hsu, J. Y. Yu, Y. C. Liang, J. H. Chen, K. M. 'Experimental Stopping Forces in Aluminum and Silver by He3/He4, Li6/Li7 and B10/B11 Ions' <i>Nucl. Inst. Methods, B241, 155-159 (2005)</i> <i>Comment : S. He3, He4, Li6, Li7, B10, B11 -&gt; Al, Ag</i>	2005-Hsu
<b>2005</b>	Zhang, Yanwen Weber, W. J. McCready, D.E. Grove, D.A. Jensen, J. 'Experimental determination of electronic stopping for ions in silicon dioxide' <i>Appl. Phys. Lett. 87, 104103 (2005)</i> <i>Comment : S. Be - Si (0.05 - 1.3 MeV/n) -&gt; SiO2</i>	2005-Zha2
<b>2007</b>	Sun, G. Döbeli, M. Müller, A.M. Stocker, M. Suter, M. 'Energy loss and straggling of heavy ions in silicon nitride in the low MeV energy range' <i>Nucl. Instrum. Methods B 256 (2007) 586 (2007)</i> <i>Comment : S, dS. Li, B, C, O, S, Fe (0.4 - 4 MeV) -&gt; silicon nitride Si3N3.1</i>	2007-Sun

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<b>Pub. Year</b>	<b>Authors, Title, Journal Citation and Comments</b>	<b>Citation Numb</b>
<b>2009</b>	Cantero, E.D. Fadanelli, R.C. Montanari, C.C. Behar, M. Eckardt, J.C. 'Experimental and theoretical study of the energy loss of Be and B ions in Zn' <i>Phys. Rev. A79, 042904 (2009)</i> <i>Comment : S. Be (52-1090 keV/u), B(45-902 keV/u) -&gt; Zn</i>	2009-CanA
<b>2010</b>	Siketic, Z. Bogdanovic Radovic, I. Alves, E. Barradas, N.P. 'Stopping power of <sup>11</sup> B in Si and TiO <sub>2</sub> measured with a bulk sample method and Bayesian inference data analysis' <i>Nucl. Instrum. Methods B 268, 1768 (2010)</i> <i>Comment : S. B (0-2.5 MeV) -&gt; Si, TiO<sub>2</sub></i>	2010-Sike

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